

SANYO

No.3688

2SC4710

NPN Triple Diffused Planar Silicon Transistor

High-Voltage Amp,
High-Voltage Switching Applications**Features**

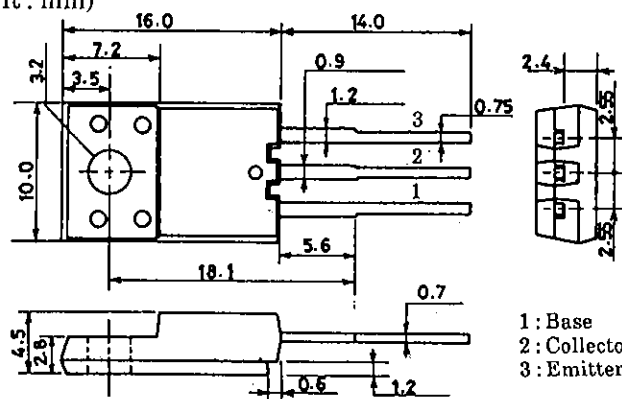
- High breakdown voltage (V_{CEO} min = 2100V).
- Small Cob (typical Cob = 1.3pF).
- Wide ASO.
- High reliability (Adoption of HVP process).
- Full isolation package.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CBO}	2100	V
Collector-to-Emitter Voltage	V_{CEO}	2100	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	10	mA
Collector Current (Pulse)	I_{CP}	30	mA
Collector Dissipation	P_C	2	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

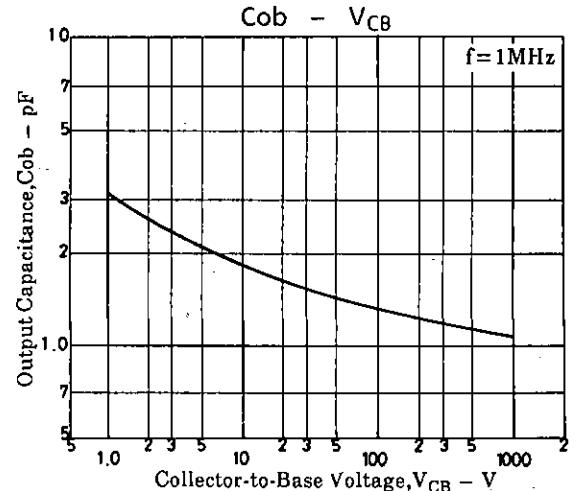
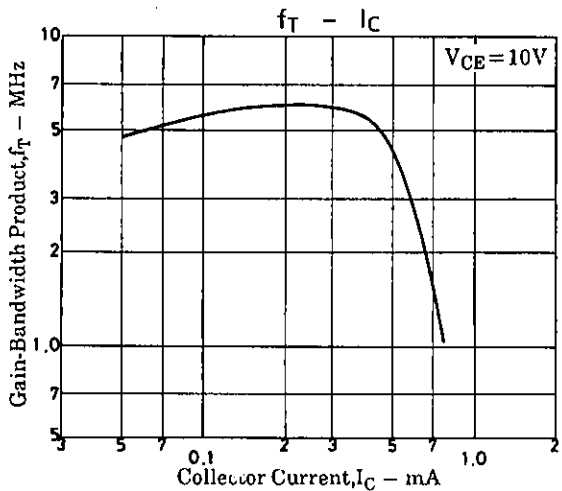
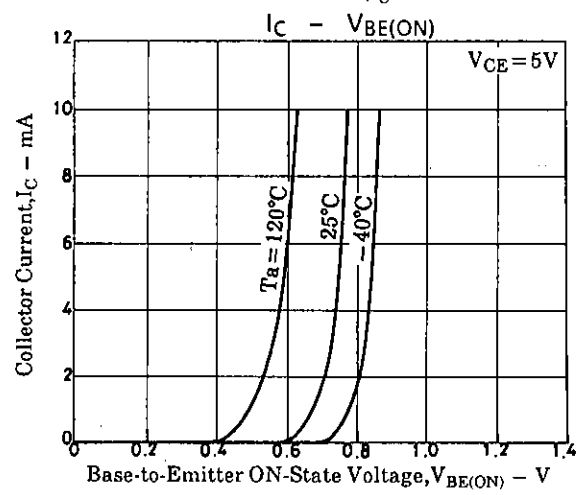
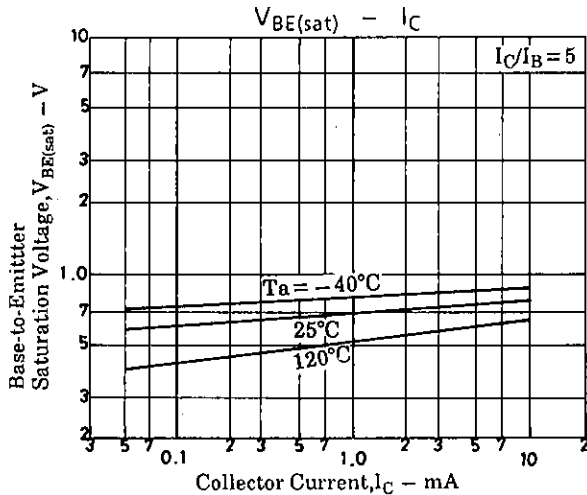
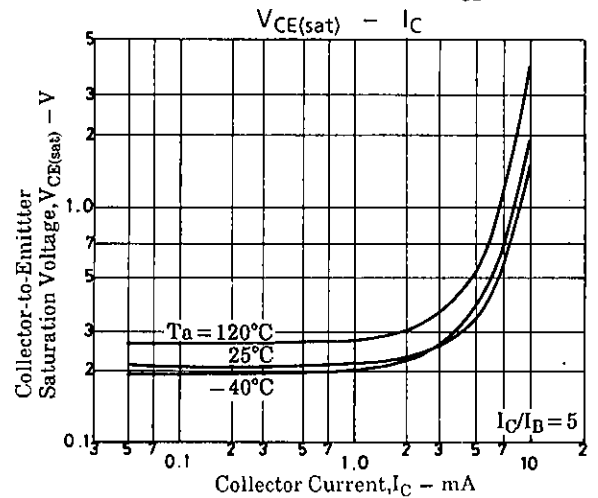
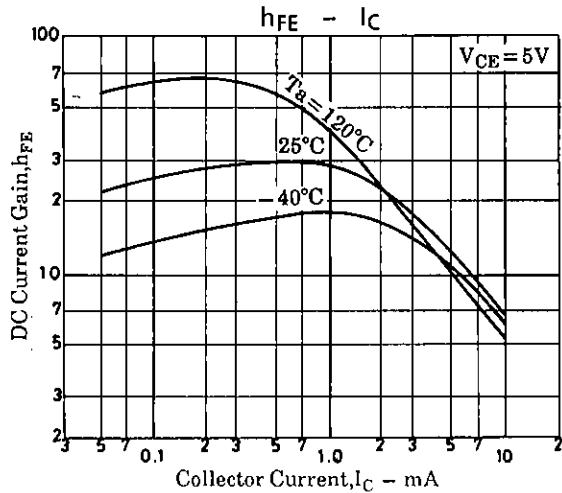
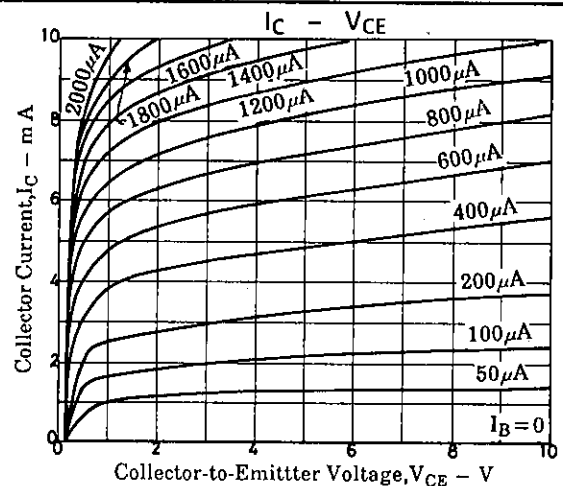
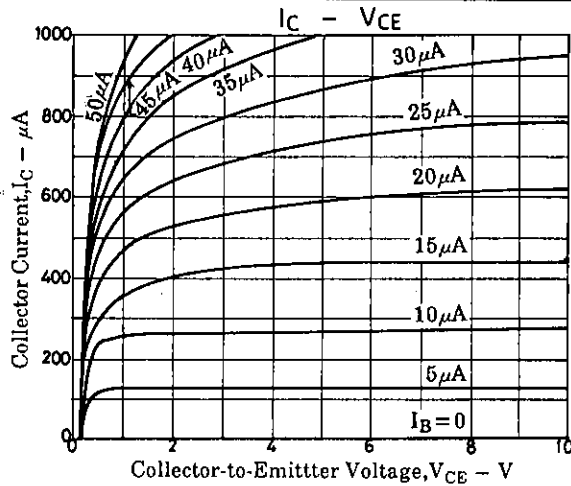
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 2100\text{V}, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 500\mu\text{A}$	10		60	
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 500\mu\text{A}$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 1\text{mA}, I_B = 200\mu\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 1\text{mA}, I_B = 200\mu\text{A}$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	2100			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\mu\text{A}, R_{BE} = \infty$	2100			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5			V
Output Capacitance	Cob	$V_{CB} = 100\text{V}, f = 1\text{MHz}$		1.3		pF

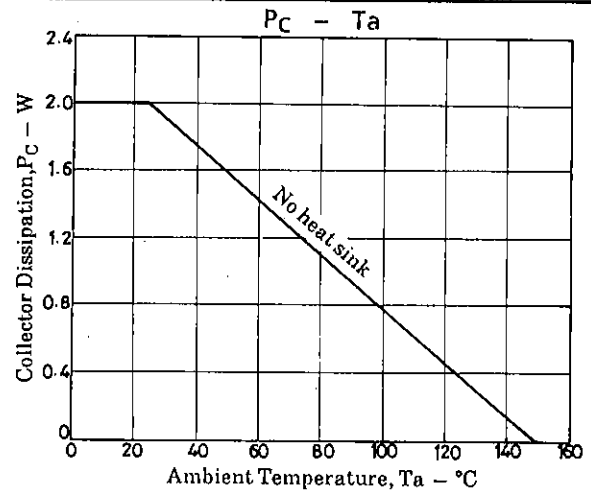
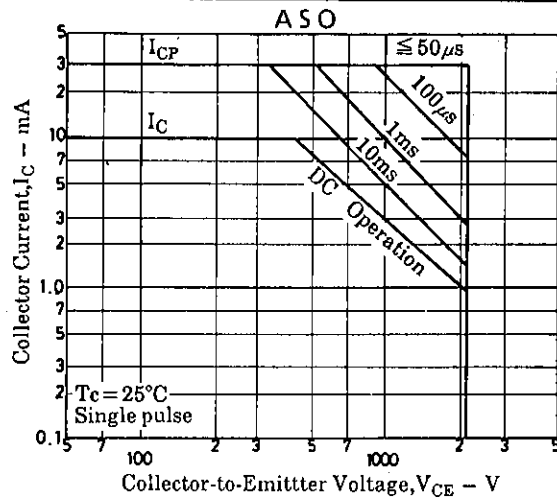
Package Dimensions 2079A
(unit: mm)1: Base
2: Collector
3: Emitter

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